

## DZ2611000L

### Silicon epitaxial planar type

For constant voltage / For surge absorption circuit  
DZ27110 in ML2 type package

#### ■ Features

- Excellent rising characteristics of zener current IZ
- Low zener operating resistance RZ
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

#### ■ Marking Symbol :PJ

#### ■ Packaging

Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

#### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation <sup>*1</sup>	PT	100	mW
Electrostatic discharge <sup>*2</sup>	ESD	±8	kV
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note) \*1 PT = 100 mW achieved with a printed circuit board.

\*2 Test method:IEC61000\_4\_2

( C = 150 pF , R = 330 Ω , Contact discharge : 10 times )

#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage <sup>*1, *2</sup>	VZ	IZ = 5 mA	10.45		11.55	V
Zener operating resistance	RZ	IZ = 5 mA			30	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			60	Ω
Reverse current	IR	VR = 8.0 V			0.05	μA
Temperature coefficient of zener voltage <sup>*3</sup>	SZ	IZ = 5 mA		8.3		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. Absolute frequency of input and output is 5 MHz.

3. \*1 The temperature must be controlled 25 °C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ ( 25 °C )

\*2 VZ guaranteed 20 ms after current flow.

\*3 Tj = 25 °C to 150 °C

